

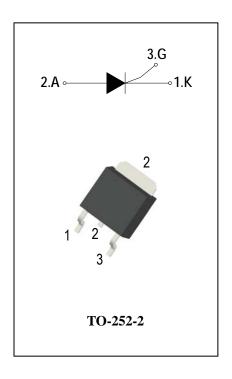
#### **SCRs**

#### **General Description**

Available either in sensitive or standard gate triggering levels, the 8A SCR series is suitable to fit all modes of control found inapplications such as overvoltage crowbar protection, motor control circuits in power tools and kitchen aids, in-rush current limiting circuits, capacitive discharge ignition, voltage regulation circuits...

#### **Features**

- ◆ Repetitive Peak Off-State Voltage: 600V and 800V
- ◆ R.M.S On-State Current (IT(RMS)= 8A)
- ♦ These are Pb-Free Devices



#### **Absolute Maximum Ratings**

Symbol	Items	Conditions		Ratings	Unit
$V_{DRM}$	Repetitive Peak Off-State Voltage	T:-25°C	ADT8A60E	600	V
$V_{RRM}$	Repetitive peak reverse voltage	Tj=25°C	ADT8A80E	800	V
I <sub>T(AV)</sub>	Average On-State Current	Half Sine Wave , Tc = 100°C		7	Α
I <sub>T(RMS)</sub>	R.M.S On-State Current	Half Sine Wave , Tc = 100°C		8	Α
I <sub>TSM</sub>	Surge On-State Current	1/2 Cycle, Sine Wave Non-Repetitive, tp=10ms(50Hz)Tj =25°C		90	А
l <sup>2</sup> t	I <sup>2</sup> t for Fusing	Tj =25°C,tp =10ms		24.5	A <sup>2</sup> S
dI/dt	Critical rate of rise of on-state current	Tj =125°C, tr≤ 100ns		50	A/µs
$P_{GM}$	Forward Peak Gate Power Dissipation	Tj =125°C, Pulse Width ≤ 20μs		5	W
$P_{G(AV)}$	Forward Average Gate Power Dissipation	Tj =25°C, tp =10ms		1	W
$I_{GM}$	Peak Gate Current	Tj =125°C, Pulse Width ≤ 20μs		4	Α
Tj	Operating Junction Temperature			- 40 ~ 125	°C
T <sub>STG</sub>	Storage Temperature			- 40 ~ 150	°C





# **ADT8A60E/80E**

## **Electrical Characteristics** (Tj = 25°C unless otherwise specified)

Symbol	Items	Conditions		ADT8A60E/80E		Unit
				Т	s	7
		$V_{DRM} = V_{RRM}, R_{GK} = 1K\Omega$			5	uA
I <sub>DRM</sub>	Peak Forward Reverse	Tj = 25°C	Max.			
I <sub>RRM</sub>	Blocking Current	$V_{DRM} = V_{RRM}, R_{GK} = 1K\Omega$ $Tj = 125^{\circ}C$	IVIAX.	2		mA
V <sub>TM</sub>	Peak On-State Voltage	I <sub>TM</sub> = 20A, t <sub>p</sub> = 380 μs	Max.	1.6		V
$V_{GD}$	Non-Trigger Gate Voltage	$V_D = V_{DRM}$ $R_L = 3.3 \text{ k}\Omega$	Min. 0.2		2	V
V GD	Non-mgger Gate Voltage	$R_{GK} = 1K\Omega$ $Tj = 125$ °C	IVIIII.			V
$V_{GT}$	Gate Trigger Voltage	Ma		1.3		V
I <sub>GT</sub>	Gate Trigger Current	$V_D = 12V$ , $R_L = 33\Omega$	Max.	c. 0.2 15		mA
I <sub>H</sub>	Holding Current	$I_T = 0.05A$ $R_{GK} = 1K\Omega$	Max.	5	40	mA
ال	Latching Current	$I_G = 1.2 I_{GT} R_{GK} = 1 K\Omega$	Max.	6	50	mA
dV/dt	Critical Rate of Rise of	$V_D = 2/3V_{DRM}$ gate open	Min.	5	150	Mus
	Off-State Voltage	$R_{GK} = 1K\Omega$ Tj = 125°C		J	150	V/µs
R <sub>th(j-c)</sub>	Junction to case		Max.	20		°C/W
R <sub>th(j-a)</sub>	Junction to ambient(Copper surface under tab:S=0.5cm²)		Max.	70		°C/W

FIG.2: Average on-state current VS Allowable

# **ADV**

FIG.1: Maximum average power dissipation (Single phase half wave)

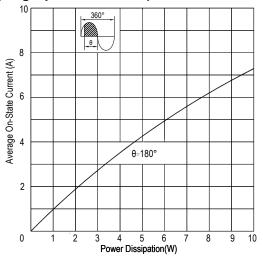


FIG.3: Gate trigger current VS Junction temperature

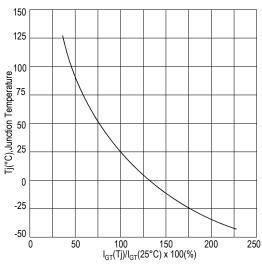


FIG.5: On-state characteristics(Max)

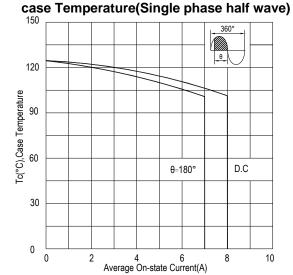
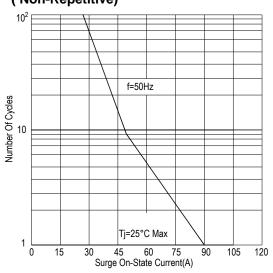


FIG.4: Rated surge on-state current (Non-Repetitive)



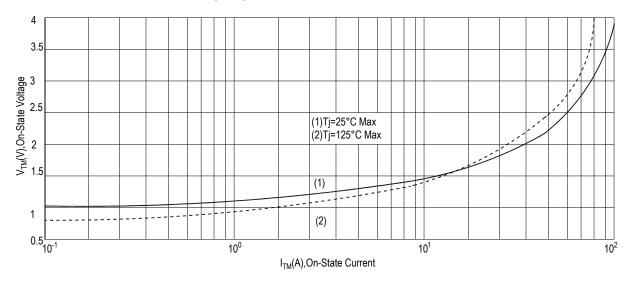






FIG.6:Holding current and Latching current VS Junction temperature

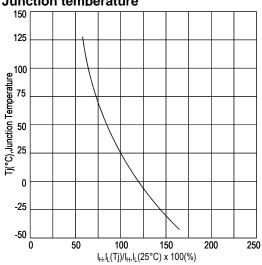


FIG.8: Gate trigger current VS Junction temperature for type T gate triggering

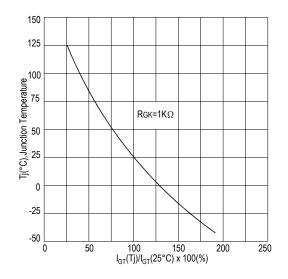


FIG.7: Gate trigger voltage VS Junction

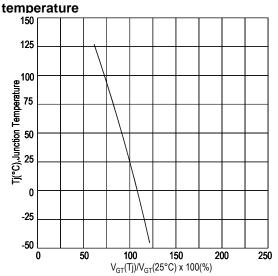
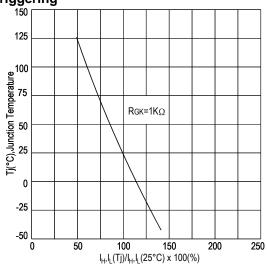


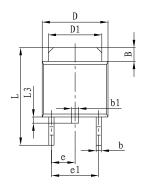
FIG.8:Holding current and Latching current
VS Junction temperature for type T gate
triggering

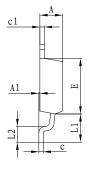


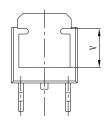


#### **PACKAGE MECHANICAL DATA**

#### **TO-252-2 Package Dimension**



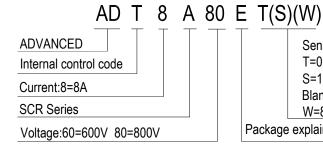




Cumb	Dimensions		Dimensions		
Symb	In Millimeters		In Inches		
ol	Min.	Max.	Min.	Max.	
Α	2.200	2.400	0.087	0.094	
A1	0.000	0.127	0.000	0.005	
В	1.350	1.650	0.053	0.065	
b	0.500	0.700	0.020	0.028	
b1	0.700	0.900	0.028	0.035	
С	0.450	0.620	0.017	0.024	
c1	0.450	0.620	0.017	0.024	
D	6.350	6.650	0.250	0.262	
D1	5.100	5.400	0.200	0.213	
E	5.900	6.200	0.232	0.244	
е	2.300 TYP.		0.091 TYP.		
e1	4.500	4.700	0.177	0.185	
L	9.500	10.60	0.374	0.396	
L1	2.550	2.900	0.100	0.114	
L2	1.400	1.780	0.055	0.070	
L3	0.600	0.900	0.024	0.035	
V	4.100	REF.	0.161 REF.		

#### **Making Diagram**





Sensitivity and type:
T=0.2mA
S=15mA
Blank=30mA
W=80mA
Package explain:E=TO-252-2

#### **Ordering information**

Part number	Package	Marking	Packing	Quantity
4 DT 9 4 60 F#	TO-252-2	ADT8A60E#	Tube	80pcs
ADT8A60E#			Embossed tape	2500pcs
ADT0 A 00F#	TO-252-2	ADT8A80E#	Tube	80pcs
ADT8A80E#			Embossed tape	2500pcs



### ADT8A60E/80E

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